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Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	To Be Assigned <u>10/752705</u>
				Filing Date	January 8, 2004
				First Named Inventor	Takashi NOGUCHI et al.
				Art Unit	2813
				Examiner Name	Jack S. J. Chen
Sheet	1	of	1	Attorney Docket Number	SON-1285/DIV

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
JC	AA	5,155,571	10/13/1992	Wang et al.	
	AB	5,241,197	08/31/1993	Murakami et al.	
	AC	5,665,616 <u>9/97</u>	08/09/1997	Kimura et al.	
	AD	5,998,807	12/07/1999	Lustig et al.	
JC	AE	US2002/0011617 A1	01/31/2002	Kubo et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
JC	CA	K. Ismail et al., "Electron transport properties of Si/SiGe heterostructures: Measurements and device Implications", Applied Physics Letters, Volume 63, August 2, 1993, Number 5, pgs. 660-662.	
	CB	L. H. Jiang, "Electrical Properties of GeSi Surface- and Buried- Channel p-MOSFET's Fabricated by Ge Implantation", IEEE Electron Devices, Volume 43, January 1996, Number 1, pgs. 97-103.	
	CC	K. Ismail et al., "High Pole Mobility In SiGe Alloys For Device Applications", Applied Physics Letters, Volume 64, June 6, 1994, Number 23, pgs. 3124-3126.	
JC	CD	J. Welser et al., "Strain Dependence of the Performance Enhancement in Strained-Si n-MOSFETs", Electron Devices Meeting, 1994, pgs. 373-376.	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Examiner Signature	/Jack Chen/ (08/06/2006)	Date Considered	08/06/2006
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